8-Channel/4-Channel Fault-Protected Analog Multiplexers

## FEATURES

All switches off with power supply off
Analog output of on channel clamped within power supplies if an overvoltage occurs
Latch-up proof construction
Low on resistance ( $270 \Omega$ typical)
Fast switching times
ton: $\mathbf{2 3 0}$ ns maximum
toff: $\mathbf{1 3 0} \mathbf{n s}$ maximum
Low power dissipation ( 3.3 mW maximum)
Fault and overvoltage protection ( -40 V to +55 V )
Break-before-make construction
TTL and CMOS compatible inputs

## APPLICATIONS

Existing multiplexer applications (both fault-protected and nonfault-protected)
New designs requiring multiplexer functions

## GENERAL DESCRIPTION

The ADG508F and ADG509F are CMOS analog multiplexers, with the ADG508F comprising eight single channels and the ADG509F comprising four differential channels. These multiplexers provide fault protection. Using a series n-channel, p-channel, n-channel MOSFET structure, both device and signal source protection is provided in the event of an overvoltage or power loss. The multiplexer can withstand continuous overvoltage inputs from -40 V to +55 V . During fault conditions with power supplies off, the multiplexer input (or output) appears as an open circuit and only a few nanoamperes of leakage current will flow. This protects not only the multiplexer and the circuitry driven by the multiplexer, but also protects the sensors or signal sources that drive the multiplexer.

The ADG508F switches one of eight inputs to a common output as determined by the 3-bit binary address lines A0, A1, and A2. The ADG509F switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines A0 and A1. An EN input on each device is used to enable or disable the device. When disabled, all channels are switched off.

## FUNCTIONAL BLOCK DIAGRAMS



Figure 1.


Figure 2.

## PRODUCT HIGHLIGHTS

1. Fault protection. The ADG508F/ADG509F can withstand continuous voltage inputs from -40 V to +55 V . When a fault occurs due to the power supplies being turned off, all the channels are turned off and only a leakage current of a few nanoamperes flows.
2. On channel saturates while fault exists.
3. Low Ron.
4. Fast switching times.
5. Break-before-make switching. Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
6. Trench isolation eliminates latch-up. A dielectric trench separates the p and n -channel MOSFETs thereby preventing latch-up.

Rev. F
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## ADG508F/ADG509F

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## SPECIFICATIONS

## DUAL SUPPLY

$\mathrm{V}_{\mathrm{DD}}=+15 \mathrm{~V} \pm 10 \%, \mathrm{~V}_{\mathrm{SS}}=-15 \mathrm{~V} \pm 10 \%$, GND $=0 \mathrm{~V}$, unless otherwise noted.
Table 1.

| Parameter | $+25^{\circ} \mathrm{C}$ | B Version $-40^{\circ} \mathrm{C} \text { to }+85^{\circ} \mathrm{C}$ | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: |
| ANALOG SWITCH <br> Analog Signal Range <br> Ron <br> Ron Drift <br> On-Resistance Match Between Channels, $\Delta$ Ron | $\begin{aligned} & V_{S S}+1.4 \\ & V_{D D}-1.4 \\ & V_{S S}+2.2 \\ & V_{D D}-2.2 \\ & 270 \\ & 0.6 \\ & 3 \end{aligned}$ | $\begin{aligned} & 350 \\ & 390 \end{aligned}$ | V typ <br> V typ <br> V typ <br> V typ <br> $\Omega$ typ <br> $\Omega$ max <br> \%/ ${ }^{\circ} \mathrm{C}$ typ <br> \% max | Output open circuit <br> Output loaded, 1 mA $\begin{aligned} & -10 \mathrm{~V} \leq \mathrm{V}_{\mathrm{s}} \leq+10 \mathrm{~V}, \mathrm{I}_{\mathrm{s}}=1 \mathrm{~mA} ; \\ & \mathrm{V}_{\mathrm{DD}}=+15 \mathrm{~V} \pm 10 \%, \mathrm{~V}_{\mathrm{SS}}=-15 \mathrm{~V} \pm 10 \% \end{aligned}$ <br> See Figure 21 $\mathrm{V}_{\mathrm{s}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{s}}=1 \mathrm{~mA}$ $\mathrm{V}_{\mathrm{s}}= \pm 10 \mathrm{~V}, \mathrm{I}_{\mathrm{s}}=-1 \mathrm{~mA}$ |
| LEAKAGE CURRENTS <br> Source Off Leakage Is (Off) <br> Drain Off Leakage $I_{D}$ (Off) ADG508F ADG509F <br> Channel On Leakage $I_{D}, I_{S}(O n)$ ADG508F <br> ADG509F | $\begin{aligned} & \pm 0.02 \\ & \pm 1 \\ & \pm 0.04 \\ & \pm 1 \\ & \pm 1 \\ & \pm 0.04 \\ & \pm 1 \\ & \pm 1 \end{aligned}$ | $\begin{aligned} & \pm 50 \\ & \pm 60 \\ & \pm 30 \\ & \\ & \pm 60 \\ & \pm 30 \end{aligned}$ | nA typ <br> nA max <br> nA typ <br> nA max <br> nA max <br> nA typ <br> nA max <br> nA max | $V_{D}= \pm 10 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}}=\mp 10 \mathrm{~V} ;$ <br> See Figure 22 $V_{D}= \pm 10 \mathrm{~V}, \mathrm{~V}_{\mathrm{S}}=\mp 10 \mathrm{~V} ;$ <br> See Figure 23 $V_{S}=V_{D}= \pm 10 \mathrm{~V} ;$ <br> See Figure 24 |
| FAULT <br> Source Leakage Current $\mathrm{I}_{\mathrm{s}}$ (Fault) (With Overvoltage) <br> Drain Leakage Current $\mathrm{I}_{\mathrm{D}}$ (Fault) (With Overvoltage) <br> Source Leakage Current Is (Fault) (Power Supplies Off) | $\begin{aligned} & \pm 0.02 \\ & \pm 2 \\ & \pm 5 \\ & \pm 2 \\ & \\ & \pm 1 \\ & \pm 2 \end{aligned}$ | $\pm 2$ | nA typ <br> $\mu \mathrm{A}$ max <br> nA typ <br> $\mu \mathrm{A}$ max <br> nA typ <br> $\mu \mathrm{A}$ max | $\mathrm{V}_{\mathrm{S}}=+55 \mathrm{~V} \text { or }-40 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=0 \mathrm{~V} \text {, see Figure } 25$ $\mathrm{V}_{\mathrm{s}}= \pm 25 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=\mp 10 \mathrm{~V} \text {, see Figure } 23$ $\mathrm{V}_{\mathrm{S}}= \pm 25 \mathrm{~V}, \mathrm{~V}_{\mathrm{D}}=\mathrm{V}_{\text {EN }}=\mathrm{A} 0, \mathrm{~A} 1, \mathrm{~A} 2=0 \mathrm{~V}$ <br> See Figure 26 |
| DIGITAL INPUTS <br> Input High Voltage, $\mathrm{V}_{\text {INH }}$ <br> Input Low Voltage, VinL <br> Input Current, $\mathrm{I}_{\mathrm{INL}}$ or $\mathrm{I}_{\mathrm{NH}}$ $\mathrm{C}_{\text {IN }}$, Digital Input Capacitance | 5 | $\begin{aligned} & 2.4 \\ & 0.8 \\ & \pm 1 \end{aligned}$ | $\vee$ min <br> $V$ max <br> $\mu \mathrm{A}$ max pF typ | $\mathrm{V}_{\mathrm{IN}}=0$ or $\mathrm{V}_{\mathrm{DD}}$ |
| DYNAMIC CHARACTERISTICS ${ }^{1}$ <br> ttransition <br> topen <br> ton (EN) <br> toff (EN) <br> $\mathrm{t}_{\text {SETT }}$, Settling Time <br> 0.1\% <br> $0.01 \%$ | $\begin{aligned} & 175 \\ & 220 \\ & 90 \\ & 60 \\ & 180 \\ & 230 \\ & 100 \\ & 130 \end{aligned}$ | $\begin{aligned} & 300 \\ & 40 \\ & 300 \\ & 150 \\ & 1 \\ & 2.5 \end{aligned}$ | ns typ <br> ns max <br> ns typ <br> ns min <br> ns typ <br> ns max <br> ns typ <br> ns max <br> us typ <br> $\mu \mathrm{styp}$ | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=1 \mathrm{M} \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S} 1}= \pm 10 \mathrm{~V}, \mathrm{~V}_{\mathrm{S} 8}=\mp 10 \mathrm{~V} \text {; see Figure } 27 \\ & \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S}}=5 \mathrm{~V} ; \text { see Figure } 28 \\ & \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S}}=5 \mathrm{~V} ; \text { see Figure } 29 \\ & \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \\ & \mathrm{~V}_{\mathrm{S}}=5 \mathrm{~V} ; \text { see Figure } 29 \\ & \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} ; \\ & \mathrm{V}_{\mathrm{S}}=5 \mathrm{~V} \end{aligned}$ |

## ADG508F/ADG509F

| Parameter | $+25^{\circ} \mathrm{C}$ | B Version $-40^{\circ} \mathrm{C} \text { to }+85^{\circ} \mathrm{C}$ | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: |
| Charge Injection | 15 |  | pC typ | $\mathrm{V}_{\mathrm{S}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{s}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}$; see Figure 30 |
| Off Isolation | 93 |  | dB typ | $\mathrm{RL}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}, \mathrm{f}=100 \mathrm{kHz} ; \mathrm{V}_{\mathrm{s}}=7 \mathrm{~V} \mathrm{rms} ;$ see Figure 31 |
| $\mathrm{C}_{s}$ (Off) | 3 |  | pF typ |  |
| $C_{\text {d }}$ (Off) |  |  |  |  |
| ADG508F | 22 |  | pF typ |  |
| ADG509F | 12 |  | pF typ |  |
| POWER REQUIREMENTS |  |  |  |  |
| ldo | 0.05 | 0.2 | mA max | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ or 5 V |
| Iss | 0.1 | 1 | $\mu \mathrm{A}$ max |  |

${ }^{1}$ Guaranteed by design, not subject to production test.

## TRUTH TABLES

Table 2. ADG508F Truth Table ${ }^{1}$

| A2 | A1 | A0 | EN | On Switch |
| :--- | :--- | :--- | :--- | :--- |
| $X$ | $X$ | $X$ | 0 | None |
| 0 | 0 | 0 | 1 | 1 |
| 0 | 0 | 1 | 1 | 3 |
| 0 | 1 | 0 | 1 | 4 |
| 0 | 1 | 1 | 1 | 5 |
| 1 | 0 | 1 | 6 |  |
| 1 | 0 | 1 | 7 |  |
| 1 | 1 | 0 | 1 | 8 |
| 1 | 1 | 1 | 1 |  |

${ }^{1} \mathrm{X}=$ don't care.

Table 3. ADG509F Truth Table ${ }^{1}$

| A1 | A0 | EN | On Switch Pair |
| :--- | :--- | :--- | :--- |
| $X$ | $X$ | 0 | None |
| 0 | 0 | 1 | 1 |
| 0 | 1 | 1 | 2 |
| 1 | 0 | 1 | 3 |
| 1 | 1 | 1 | 4 |

[^0]
## ADG508F/ADG509F

## ABSOLUTE MAXIMUM RATINGS

$\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted.
Table 4.

| Parameter | Rating |
| :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}$ to $\mathrm{V}_{\text {SS }}$ | 48 V |
| $V_{\text {DD }}$ to GND | -0.3 V to +48 V |
| $V_{\text {ss }}$ to GND | +0.3 V to -48 V |
| Digital Input, EN, Ax | $-0.3 \mathrm{~V} \text { to } \mathrm{V}_{\mathrm{DD}}+0.3 \mathrm{~V} \text { or }$ <br> 20 mA , whichever occurs first |
| $\mathrm{V}_{\mathrm{s}}$, Analog Input Overvoltage with Power On $\left(\mathrm{V}_{\mathrm{DD}}=+15 \mathrm{~V}, \mathrm{~V}_{S S}=-15 \mathrm{~V}\right)$ | $\mathrm{V}_{S S}-25 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{DD}}+40 \mathrm{~V}$ |
| $\mathrm{V}_{\mathrm{s}}$, Analog Input Overvoltage with Power Off ( $\mathrm{V}_{\mathrm{DD}}=0 \mathrm{~V}, \mathrm{~V}_{S S}=0 \mathrm{~V}$ ) | -40 V to +55 V |
| Continuous Current, S or D | 20 mA |
| Peak Current, S or D <br> (Pulsed at 1 ms, 10\% Duty Cycle Max) | 40 mA |
| Operating Temperature Range Industrial (B Version) | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Junction Temperature | $150^{\circ} \mathrm{C}$ |
| TSSOP |  |
| $\theta_{\text {JA }}$, Thermal Impedance | $112^{\circ} \mathrm{C} / \mathrm{W}$ |
| Plastic DIP Package |  |
| $\theta_{\mathrm{J} A}$, Thermal Impedance <br> 16-Lead | $117^{\circ} \mathrm{C} / \mathrm{W}$ |
| SOIC Package |  |
| $\theta_{\text {JA }}$, Thermal Impedance |  |
| Narrow Body | $77^{\circ} \mathrm{C} / \mathrm{W}$ |
| Wide Body | $75^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ESD CAUTION

|  | ESD (electrostatic discharge) sensitive device. <br> Charged devices and circuit boards can discharge <br> without detection. Although this product features <br> patented or proprietary protection circuitry, damage <br> may occur on devices subjected to high energy ESD. <br> Therefore, proper ESD precautions should be taken to <br> avoid performance degradation or loss of functionality. |
| :--- | :--- |

## ADG508F/ADG509F

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

| A0 1 | $\begin{aligned} & \text { ADG508F } \\ & \text { TOP VIEW } \\ & \text { (Not to Scale) } \end{aligned}$ | 16 | A1 |
| :---: | :---: | :---: | :---: |
| EN 2 |  | 15 | A2 |
| $\mathrm{V}_{\text {SS }} 3$ |  | 14 | GND |
| S1 |  | 13 | $V_{D D}$ |
| S2 5 |  | 12 | S5 |
| S3 6 |  | 11 | S6 |
| S4 7 |  | 10 | S7 |
| D 8 |  | 9 | S8 |

Figure 3. ADG508F Pin Configuration

Table 5. ADG508F Pin Function Descriptions

| Pin No. | Mnemonic | Description |
| :--- | :--- | :--- |
| 1 | A0 | Logic Control Input. |
| 2 | EN | Active High Digital Input. When low, the device is disabled and all switches are off. When high, <br> Ax logic inputs determine on switches. <br> Most Negative Power Supply Potential. In single-supply applications, this pin can be connected <br> to ground. |
| 3 | VS | Source Terminal 1. This pin can be an input or an output. |
| 4 | S1 | Source Terminal 2. This pin can be an input or an output. |
| 5 | S2 | Source Terminal 3. This pin can be an input or an output. |
| 6 | S3 | Source Terminal 4. This pin can be an input or an output. |
| 7 | S4 | Drain Terminal. This pin can be an input or an output. |
| 8 | S8 | Source Terminal 8. This pin can be an input or an output. |
| 9 | S7 | Source Terminal 7. This pin can be an input or an output. |
| 10 | S6 | Source Terminal 6. This pin can be an input or an output. |
| 11 | S5 | Source Terminal 5. This pin can be an input or an output. |
| 12 | VDD | Most Positive Power Supply Potential. |
| 13 | GND | Ground (0V) Reference. |
| 14 | A2 | Logic Control Input. |
| 15 | Logic Control Input. |  |
| 16 |  |  |



Figure 4. ADG509F Pin Configuration

Table 6. ADG509F Pin Function Descriptions

| Pin No. | Mnemonic | Description |
| :--- | :--- | :--- |
| 1 | AO | Logic Control Input. <br> Active High Digital Input. When low, the device is disabled and all switches are off. When high, <br> Ax logic inputs determine on switches. <br> 2 |
| 3 | EN | Most Negative Power Supply Potential. In single-supply applications, this pin can be connected <br> to ground. |
| 4 | VSS | Source Terminal 1A. This pin can be an input or an output. |
| 5 | S2A | Source Terminal 2A. This pin can be an input or an output. |
| 6 | S3A | Source Terminal 3A. This pin can be an input or an output. |
| 7 | S4A | Source Terminal 4A. This pin can be an input or an output. |
| 8 | DA | Drain Terminal A. This pin can be an input or an output. |
| 9 | DB | Drain Terminal B. This pin can be an input or an output. |
| 10 | S4B | Source Terminal 4B. This pin can be an input or an output. |
| 11 | S3B | Source Terminal 3B. This pin can be an input or an output. |
| 12 | S2B | Source Terminal 2B. This pin can be an input or an output. |
| 13 | S1B | Source Terminal 1B. This pin can be an input or an output. |
| 14 | VDD | Most Positive Power Supply Potential. |
| 15 | GND | Ground (O V) Reference. |
| 16 | A1 | Logic Control Input. |

## ADG508F/ADG509F

## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 5. On Resistance as a Function of $V_{D}\left(V_{S}\right)$


Figure 6. Source Input Leakage Current as a Function of $V_{s}$ (Power Supplies Off) During Overvoltage Conditions


Figure 7. Drain Output Leakage Current as a Function of Vs (Power Supplies On) During Overvoltage Conditions


Figure 8. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ for Different Temperatures


Figure 9. Source Input Leakage Current as a Function of $V_{s}$ (Power Supplies On) During Overvoltage Conditions


Figure 10. Leakage Currents as a Function of $V_{D}\left(V_{S}\right)$

## ADG508F/ADG509F



Figure 11. Leakage Currents as a Function of Temperature


Figure 12. Switching Time vs. Dual Power Supply


Figure 13. Switching Time vs. Temperature


Figure 14. Off Isolation vs. Frequency, $\pm 15$ V Dual Supply


Figure 15. Capacitance vs. Source Voltage


Figure 16. Charge Injection vs. Source Voltage

## ADG508F/ADG509F

## TERMINOLOGY

$V_{D D}$
Most positive power supply potential.
Vss
Most negative power supply potential.
GND
Ground (0 V) reference.
Ron
Ohmic resistance between D and S.

## Ron Drift

Percentage change in Ron when temperature changes by one degree Celsius.

## $\Delta \mathbf{R}_{\text {ON }}$

$\Delta \mathrm{R}_{\text {on }}$ represents the difference between the Ron of any two channels as a percentage of the maximum Ron of those two channels.
Is (Off)
Source leakage current when the switch is off.
$\mathrm{I}_{\mathrm{D}}$ (Off)
Drain leakage current when the switch is off.

## $\mathrm{I}_{\mathrm{D}}, \mathrm{I}_{\mathrm{S}}(\mathbf{O n})$

Channel leakage current when the switch is on.

## Is (Fault—Power Supplies On)

Source leakage current when exposed to an overvoltage condition.
$\mathrm{I}_{\mathrm{D}}$ (Fault-Power Supplies On)
Drain leakage current when exposed to an overvoltage condition.

## Is (Fault-Power Supplies Off)

Source leakage current with power supplies off.
$V_{D}$ (Vs)
Analog Voltage on Terminals D, S.
Cs (Off)
Channel input capacitance for off condition.

## $\mathrm{C}_{\mathrm{b}}$ (Off)

Channel output capacitance for off condition.
$\mathrm{C}_{\text {in }}$
Digital input capacitance.
$t_{\text {ON }}$ (EN)
Delay time between the $50 \%$ and $90 \%$ points of the digital input and switch on condition.
$t_{\text {off }}$ (EN)
Delay time between the $50 \%$ and $90 \%$ points of the digital input and switch off condition.
$\mathbf{t}_{\text {transition }}$
Delay time between the $50 \%$ and $90 \%$ points of the digital inputs and the switch on condition when switching from one address state to another.
$t_{\text {open }}$
Off time measured between $80 \%$ points of both switches when switching from one address state to another.
$V_{\text {INL }}$
Maximum input voltage for Logic 0 .
$\mathrm{V}_{\mathrm{INH}}$
Minimum input voltage for Logic 1.
$\mathrm{I}_{\text {INL }}\left(\mathrm{I}_{\text {INH }}\right)$
Input current of the digital input.

## Off Isolation

A measure of unwanted signal coupling through an off channel.

## Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.
IDD
Positive supply current.
Iss
Negative supply current.

## ADG508F/ADG509F

## THEORY OF OPERATION

The ADG508F/ADG509F multiplexers are capable of withstanding overvoltages from -40 V to +55 V , irrespective of whether the power supplies are present or not. Each channel of the multiplexer consists of an n-channel MOSFET, a p-channel MOSFET, and an n-channel MOSFET, connected in series. When the analog input exceeds the power supplies, one of the MOSFETs will saturate limiting the current. The current during a fault condition is determined by the load on the output. Figure 17 illustrates the channel architecture that enables these multiplexers to withstand continuous overvoltages.
When an analog input of $\mathrm{V}_{\mathrm{SS}}+2.2 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{DD}}-2.2 \mathrm{~V}$ (output loaded, 1 mA ) is applied to the ADG508F/ADG509F, the multiplexer behaves as a standard multiplexer, with specifications similar to a standard multiplexer, for example, the on-resistance is $390 \Omega$ maximum. However, when an overvoltage is applied to the device, one of the three MOSFETs saturate.

Figure 17 to Figure 20 show the conditions of the three MOSFETs for the various overvoltage situations. When the analog input applied to an on channel approaches the positive power supply line, the n-channel MOSFET saturates because the voltage on the analog input exceeds the difference between $V_{D D}$ and the n -channel threshold voltage ( $\mathrm{V}_{\text {TN }}$ ). When a voltage more negative than $V_{s s}$ is applied to the multiplexer, the p-channel MOSFET will saturate because the analog input is more negative than the difference between $\mathrm{V}_{\mathrm{ss}}$ and the p-channel threshold voltage $\left(\mathrm{V}_{\mathrm{TP}}\right)$. Because $\mathrm{V}_{\mathrm{TN}}$ is nominally 1.4 V and $\mathrm{V}_{\mathrm{TP}}-1.4 \mathrm{~V}$, the analog input range to the multiplexer is limited to $\mathrm{V}_{\mathrm{SS}}+1.4 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{DD}}-1.4 \mathrm{~V}$ (output open circuit) when a $\pm 15 \mathrm{~V}$ power supply is used.
When the power supplies are present but the channel is off, again either the p-channel MOSFET or one of the n-channel MOSFETs will remain off when an overvoltage occurs.

Finally, when the power supplies are off, the gate of each MOSFET will be at ground. A negative overvoltage switches on the first n-channel MOSFET but the bias produced by the overvoltage causes the p-channel MOSFET to remain turned off. With a positive overvoltage, the first MOSFET in the series will remain off because the gate to source voltage applied to this MOSFET is negative.

During fault conditions (power supplies off), the leakage current into and out of the ADG508F/ADG509F is limited to a few microamps. This protects the multiplexer and succeeding circuitry from over stresses as well as protecting the signal sources which drive the multiplexer. Also, the other channels of the multiplexer will be undisturbed by the overvoltage and will continue to operate normally.


Figure 17. +55 V Overvoltage Input to the On Channel


Figure 18. -40 V Overvoltage on an Off Channel with Multiplexer Power On


Figure 19. +55 V Overvoltage with Power Off


Figure 20. -40 V Overvoltage with Power Off

## ADG508F/ADG509F

TEST CIRCUITS


Figure 21. On Resistance


Figure 22. Is (Off)


Figure 23. $I_{D}$ (Off)


Figure 24. ID (On)


Figure 25. Input Leakage Current (with Overvoltage)


Figure 26. Input Leakage Current (with Power Supplies Off)


Figure 27. Switching Time of Multiplexer, $t_{\text {TRANSITION }}$


Figure 28. Break-Before-Make Delay, topen


Figure 29. Enable Delay, $t_{\text {ON }}(E N)$, $t_{\text {OFF }}(E N)$

## ADG508F/ADG509F


*SIMILAR CONNECTION FOR ADG509F.
Figure 30. Charge Injection


Figure 31. Off Isolation

## OUTLINE DIMENSIONS



CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.
Figure 32. 16-Lead Plastic Dual In-Line Package [PDIP] Narrow Body ( N -16)
Dimensions shown in inches and (millimeters)


COMPLIANT TO JEDEC STANDARDS MS-012-AC
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.
Figure 33. 16-Lead Standard Small Outline Package [SOIC_N] Narrow Body

$$
(R-16)
$$

Dimensions shown in millimeters and (inches)

## ADG508F/ADG509F



Figure 34. 16-Lead Standard Small Outline Package [SOIC_W] Wide Body ( $R W$-16)
Dimensions shown in millimeters and (inches)


Figure 35. 16-Lead Thin Shrink Small Outline Package [TSSOP] ( $R U-16$ )
Dimensions shown in millimeters

## ADG508F/ADG509F

## ORDERING GUIDE

| Model $^{1}$ | Temperature Range | Package Description | Package Option |
| :--- | :--- | :--- | :--- |
| ADG508FBNZ $_{\text {ADG508FBRN }}$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead PDIP | $\mathrm{N}-16$ |
| ADG508FBRNZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_N | R-16 |
| ADG508FBRNZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_N | R-16 |
| ADG508FBRWZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_N | R-16 |
| ADG508FBRWZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_W | RW-16 |
| ADG508FBRUZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_W | RW-16 |
| ADG508FBRUZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead TSSOP | RU-16 |
| ADG509FBNZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead TSSOP | RU-16 |
| ADG509FBRN | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead PDIP | $\mathrm{N}-16$ |
| ADG509FBRNZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_N | R-16 |
| ADG509FBRNZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_N | R-16 |
| ADG509FBRWZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_N | R-16 |
| ADG509FBRWZ-REEL | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead SOIC_W | RW-16 |
| ADG509FBRUZ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16-Lead SOIC_W | RW-16 |
| ADG509FBRUZ-REEL7 | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 16 -Lead TSSOP | RU-16 |

${ }^{1} Z=$ RoHS Compliant Part.

## ADG508F/ADG509F

## NOTES

NOTES

## ADG508F/ADG509F

## NOTES

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HEF4053BT. 653 ADG5408BRUZ-REEL7 ADG1404YRUZ-REEL7 ADG1208YRZ-REEL7 MAX4704EUB+T ADG1406BRUZ-REEL7
LTC4305IDHD\#PBF CD4053BPWRG4 74HC4053D. 653 74LVC2G53DP. 125 74HC4052DB. 112 74HC4052PW. 112 74HC4053DB. 112
74HC4067DB. 112 74HC4351DB. 112 74HCT4052D. 112 74HCT4052DB. 112 74HCT4053DB. 112 74HCT4067D.112 74HCT4351D. 112
74LV4051PW. 112 FSA1256L8X_F113 PI5V330QE PI5V331QE 5962-8771601EA 5962-87716022A ADG5249FBRUZ ADG1438BRUZ
AD7506JNZ AD7506KNZ


[^0]:    ${ }^{1} \mathrm{X}=$ don't care.

